Varian Gen 1.5 Molecular-Beam Epitaxial Reactor

Ultra-high vacuum system for growing a variety of compound semiconductor films such as GaAs, AlGaAs, InGaAs and GaAsN.

Features:

- 2” diameter rotatable wafer capability
- High temperature 2.75” Conflat effusion cells (Ga, Al, In, As, Si, and Be)
- Hot-lipped Ga cell
- Nitrogen cracker for nitride growths
- Computer controlled shutters with programmable recipes
- Cryo and ion pumping of both the growth and loadlock chambers
- Beam-flux monitoring capability
- Refection high-energy electron diffraction (RHEED)
- Quadrapole mass spectroscopy (QMS)
- 6-wafer loading carousel with bakeout
- Fully bakeable systems to 200C